TOSHIBA BI-DIRECTIONAL TRIODE THYRISTOR SILICON PLANAR TYPE

SM12G48, USM12G48, SM12J48, USM12J48 SM12G48A, USM12G48A, SM12J48A, USM12J48A

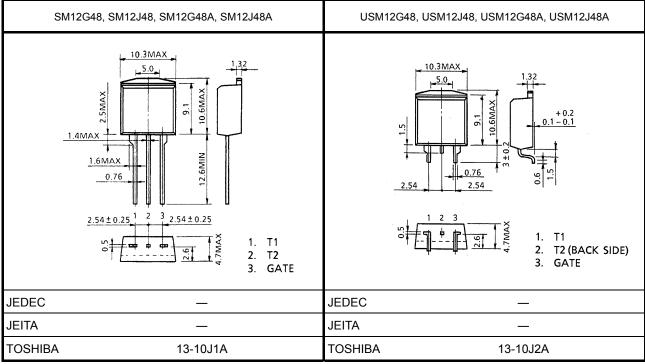
AC POWER CONTROL APPLICATIONS

Repetitive Peak Off-State Voltage : VDRM=400V, 600V
 R.M.S. On-State Current : IT (RMS) =12A

• Gate Trigger Current : I_{GT}=30mA Max.

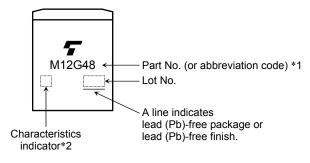
: I_{GT}=20mA Max. ("A"Type)

Unit: mm



Weight: 1.7g

MARKING



	Part No. (or abbreviation code)	Part No.		
*1	M12G48	SM12G48, SM12G48A		
	WIIZO40	USM12G48, USM12G48A		
	M12J48	SM12J48, SM12J48A		
		USM12J48, USM12J48A		
*2	Nothing	SM12G48, SM12J48		
	Nothing	USM12G48, USM12J48		
	А	SM12G48A, SM12J48A		
		USM12G48A, USM12J48A		

ABSOLUTE MAXIMUM RATINGS

CHARACTI	ERISTIC	SYMBOL	RATING	UNIT	
Repetitive Peak	(U)SM12G48 (U)SM12G48A	V_{DRM}	400	V	
Off-State Voltage	(U)SM12J48 (U)SM12J48A	¥ DRM	600	V	
R.M.S On-State Curr	ent	I _{T (RMS)}	12	Α	
Peak One Cycle Sur	ge On-State	I _{TSM}	120 (50Hz)	А	
Current (Non-Repetit	tive)		132 (60Hz)	4	
I ² t Limit Value		1 ² t	72	A ² s	
Critical Rate of Rise On-State Current	of (Note 1)	di /dt	50	A / μs	
Peak Gate Power Di	ssipation	P_{GM}	5	W	
Average Gate Power	Dissipation	P _G (AV)	0.5	W	
Peak Forward Gate	√oltage	V_{GM}	10	V	
Peak Forward Gate	Current	I _{GM}	2	Α	
Junction Temperatur	е	Tj	-40~125	°C	
Storage Temperature	e Range	T _{stg}	-40~125	°C	

Note 1: V_{DRM}=0.5×Rated

 $I_{TM} \le 15A$ $t_{gw} \ge 10 \mu s$ $t_{gr} \le 250 ns$ $i_{qp} = I_{GT} \times 2.0$

Note 2: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

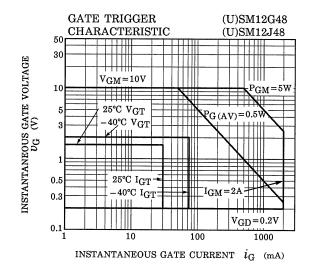
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

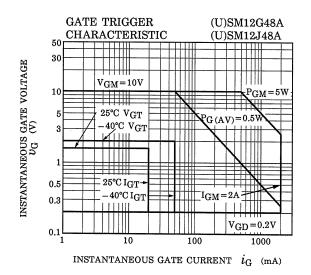
TOSHIBA SM12(G,J)48,USM12(G,J)48,SM12(G,J)48A,USM12(G,J)48A

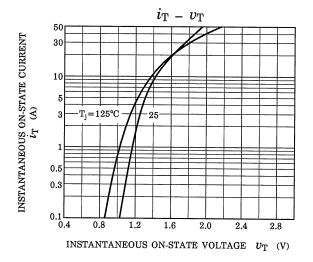
ELECTRICAL CHARACTERISTICS (Ta=25°C)

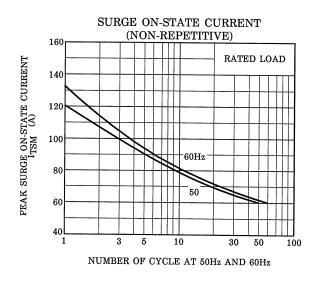
CHARACTERISTIC			SYMBOL	TEST CONDITION		MIN.	TYP.	MAX.	UNIT	
Repetitive Peak Off-State Current			I _{DRM}	V _{DRM} =Rated		_	_	20	μА	
Gate Trigger Voltage II III IV		V _{GT}	V_D =12 V R_L =20 Ω	T2 (+) , Gate (+)	_	_	1.5	V		
				T2 (+) , Gate (-)	_	_	1.5			
				T2 (-) , Gate (-)	_	_	1.5			
				T2 (-) , Gate (+)	_	_	_			
Gate Trigger Current		SM12G48 SM12J48			V _D =12V	T2 (+) , Gate (+)	_	_	30	mA
	SM12					T2 (+) , Gate (-)	_	_	30	
	SM12					T2 (-) , Gate (-)	_	_	30	
						T2 (-) , Gate (+)	_	_	_	
			I	IGT	R _L =20Ω	T2 (+) , Gate (+)	_	_	20	IIIA
	SM12	SM12G48A	II			T2 (+) , Gate (-)	_	_	20	
	SM12	2J48A	III			T2 (-) , Gate (-)	_	_	20	
						T2 (-) , Gate (+)	_	_	_	
Peak On-State Voltage			V _{TM}	I _{TM} =17A		_	_	1.5	V	
Gate Non-Trigge	r Voltag	je		V_{GD}	V _D =Rated, Tc=125°C		0.2	_	_	٧
Holding Current				lΗ	V _D =12V, I _{TM} =1A		_	_	50	mA
Thermal Resistance			R _{th (j-c)}	Junction to Case, AC		_	_	2.4	°C/W	
Critical Rate of Rise of		(U)SM12G48 (U)SM12J48		dv / dt	V _{DRM} =Rated, T _i =125°C		_	300	_	- V / μs
Off-State Voltage	e 	(U)SM12G48A (U)SM12J48A		uv / ut	Exponential Rise		_	200	_	ν / μο
Critical Rate of R				(dv / dt) c	V _{DRM} =400V, T _i =125°C		10	_	_	· V / μs
Off-State Voltage at Commutation		(U)SM12G48A (U)SM12J48A		(uv / ut) c	(di / dt) c=-6.5Å / ms		4	_	_	ν / μδ

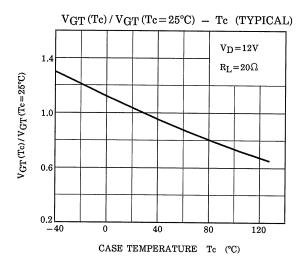
TOSHIBA SM12(G,J)48,USM12(G,J)48,SM12(G,J)48A,USM12(G,J)48A

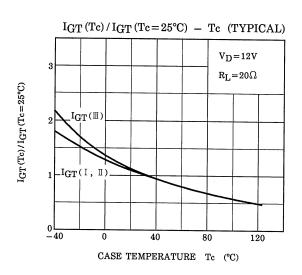




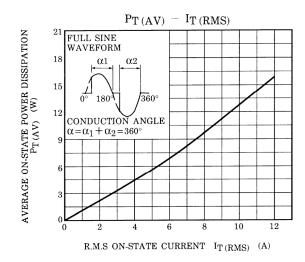


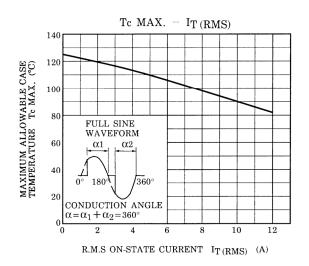


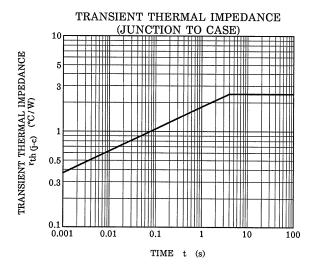


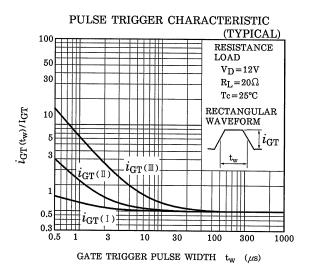


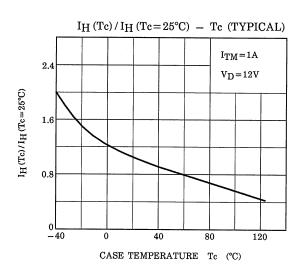
TOSHIBA SM12(G,J)48,USM12(G,J)48,SM12(G,J)48A,USM12(G,J)48A











RESTRICTIONS ON PRODUCT USE

20070701-EN

- The information contained herein is subject to change without notice.
- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property.
 In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc.
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in his document shall be made at the customer's own risk.
- The products described in this document shall not be used or embedded to any downstream products of which
 manufacture, use and/or sale are prohibited under any applicable laws and regulations.
- The information contained herein is presented only as a guide for the applications of our products. No
 responsibility is assumed by TOSHIBA for any infringements of patents or other rights of the third parties which
 may result from its use. No license is granted by implication or otherwise under any patents or other rights of
 TOSHIBA or the third parties.
- Please contact your sales representative for product-by-product details in this document regarding RoHS
 compatibility. Please use these products in this document in compliance with all applicable laws and regulations
 that regulate the inclusion or use of controlled substances. Toshiba assumes no liability for damage or losses
 occurring as a result of noncompliance with applicable laws and regulations.